

**Silicon PNP Power Transistor**

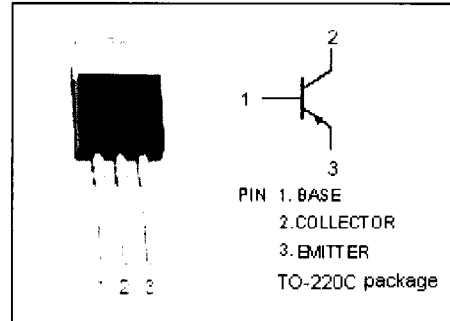
**2SA671**

**DESCRIPTION**

- Low Collector Saturation Voltage-  
 :  $V_{CE(SUS)} = -1.0V(\text{Max}) @ I_C = -2.0A$
- DC Current Gain  
 :  $h_{FE} = 35-320 @ I_C = -0.5A$
- Complement to Type 2SC1061

**APPLICATIONS**

- Designed for use in low frequency power amplifier applications.

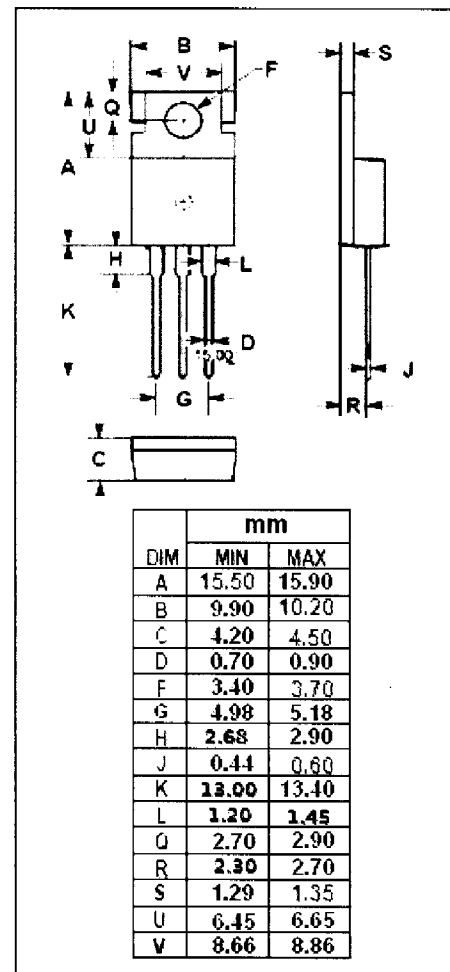


**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

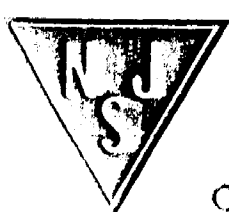
SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-4	V
$I_C$	Collector Current-Continuous	-3	A
$I_{CM}$	Collector Current-Peak	-6	A
$I_B$	Base Current-Continuous	-0.5	A
$P_C$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	25	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	5.0	$^\circ\text{C/W}$



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# 2SA671

## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}; I_B = 0$	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -5\text{mA}; I_C = 0$	-7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -1\text{A}; V_{CE} = -4\text{V}$			-1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -25\text{V}; I_E = 0$			-100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-100	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C = -0.1\text{A}; V_{CE} = -4\text{V}$	35		320	
$h_{FE-2}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	35			
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -4\text{V}; f_{test} = 1\text{MHz}$	5			MHz

### ◆ $h_{FE-1}$ Classifications

A	B	C	D
35-70	60-120	100-200	160-320